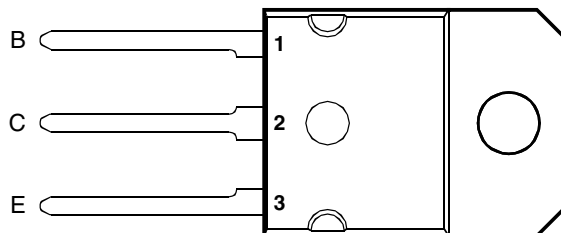


- Designed for Complementary Use with BDW83, BDW83A, BDW83B, BDW83C and BDW83D
- 150 W at 25°C Case Temperature
- 15 A Continuous Collector Current
- Minimum h_{FE} of 750 at 3V, 6 A

SOT-93 PACKAGE
(TOP VIEW)



Pin 2 is in electrical contact with the mounting base.

MDTRAAA

absolute maximum ratings at 25°C case temperature (unless otherwise noted)

RATING		SYMBOL	VALUE	UNIT
Collector-base voltage ($I_E = 0$)	BDW84	V_{CBO}	-45	V
	BDW84A		-60	
	BDW84B		-80	
	BDW84C		-100	
	BDW84D		-120	
Collector-emitter voltage ($I_B = 0$) (see Note 1)	BDW84	V_{CEO}	-45	V
	BDW84A		-60	
	BDW84B		-80	
	BDW84C		-100	
	BDW84D		-120	
Emitter-base voltage		V_{EBO}	-5	V
Continuous collector current		I_C	-15	A
Continuous base current		I_B	-0.5	A
Continuous device dissipation at (or below) 25°C case temperature (see Note 2)		P_{tot}	150	W
Continuous device dissipation at (or below) 25°C free air temperature (see Note 3)		P_{tot}	3.5	W
Unclamped inductive load energy (see Note 4)		$\frac{1}{2}LI_C^2$	100	mJ
Operating junction temperature range		T_j	-65 to +150	°C
Operating temperature range		T_{stg}	-65 to +150	°C
Operating free-air temperature range		T_A	-65 to +150	°C

- NOTES: 1. These values apply when the base-emitter diode is open circuited.
 2. Derate linearly to 150°C case temperature at the rate of 1.2 W/°C.
 3. Derate linearly to 150°C free air temperature at the rate of 28 mW/°C.
 4. This rating is based on the capability of the transistor to operate safely in a circuit of: L = 20 mH, $I_{B(on)} = -5$ mA, $R_{BE} = 100 \Omega$, $V_{BE(off)} = 0$, $R_S = 0.1 \Omega$, $V_{CC} = -20$ V.

PRODUCT INFORMATION

electrical characteristics at 25°C case temperature (unless otherwise noted)

PARAMETER	TEST CONDITIONS			MIN	TYP	MAX	UNIT
$V_{(BR)CEO}$ Collector-emitter breakdown voltage	$I_C = -30 \text{ mA}$	$I_B = 0$	(see Note 5)	BDW84 BDW84A BDW84B BDW84C BDW84D			V
I_{CEO} Collector-emitter cut-off current	$V_{CE} = -30 \text{ V}$ $V_{CE} = -30 \text{ V}$ $V_{CE} = -40 \text{ V}$ $V_{CE} = -50 \text{ V}$ $V_{CE} = -60 \text{ V}$	$I_B = 0$ $I_B = 0$ $I_B = 0$ $I_B = 0$ $I_B = 0$		BDW84 BDW84A BDW84B BDW84C BDW84D		-1 -1 -1 -1 -1	mA
I_{CBO} Collector cut-off current	$V_{CB} = -45 \text{ V}$ $V_{CB} = -60 \text{ V}$ $V_{CB} = -80 \text{ V}$ $V_{CB} = -100 \text{ V}$ $V_{CB} = -120 \text{ V}$ $V_{CB} = -45 \text{ V}$ $V_{CB} = -60 \text{ V}$ $V_{CB} = -80 \text{ V}$ $V_{CB} = -100 \text{ V}$ $V_{CB} = -120 \text{ V}$	$I_E = 0$ $I_E = 0$ $I_E = 0$ $I_E = 0$ $I_E = 0$ $I_E = 0$ $I_E = 0$ $I_E = 0$ $I_E = 0$ $I_E = 0$	$T_C = 150^\circ\text{C}$ $T_C = 150^\circ\text{C}$ $T_C = 150^\circ\text{C}$ $T_C = 150^\circ\text{C}$ $T_C = 150^\circ\text{C}$	BDW84 BDW84A BDW84B BDW84C BDW84D BDW84 BDW84A BDW84B BDW84C BDW84D		-0.5 -0.5 -0.5 -0.5 -0.5 -5 -5 -5 -5 -5	mA
I_{EBO} Emitter cut-off current	$V_{EB} = -5 \text{ V}$	$I_C = 0$				-2	mA
h_{FE} Forward current transfer ratio	$V_{CE} = -3 \text{ V}$ $V_{CE} = -3 \text{ V}$	$I_C = -6 \text{ A}$ $I_C = -15 \text{ A}$	(see Notes 5 and 6)	750 100		20000	
$V_{BE(on)}$ Base-emitter voltage	$V_{CE} = -3 \text{ V}$	$I_C = -6 \text{ A}$	(see Notes 5 and 6)			-2.5	V
$V_{CE(sat)}$ Collector-emitter saturation voltage	$I_B = -12 \text{ mA}$ $I_B = -150 \text{ mA}$	$I_C = -6 \text{ A}$ $I_C = -15 \text{ A}$	(see Notes 5 and 6)			-2.5 -4	V
V_{EC} Parallel diode forward voltage	$I_E = -15 \text{ A}$	$I_B = 0$				-3.5	V

NOTES: 5. These parameters must be measured using pulse techniques, $t_p = 300 \mu\text{s}$, duty cycle $\leq 2\%$.

6. These parameters must be measured using voltage-sensing contacts, separate from the current carrying contacts.

thermal characteristics

PARAMETER	MIN	TYP	MAX	UNIT
$R_{\theta JC}$ Junction to case thermal resistance			0.83	$^\circ\text{C/W}$
$R_{\theta JA}$ Junction to free air thermal resistance			35.7	$^\circ\text{C/W}$

resistive-load-switching characteristics at 25°C case temperature

PARAMETER	TEST CONDITIONS †			MIN	TYP	MAX	UNIT
t_{on} Turn-on time	$I_C = -10 \text{ A}$	$I_{B(on)} = -40 \text{ mA}$	$I_{B(off)} = 40 \text{ mA}$		0.9		μs
t_{off} Turn-off time	$V_{BE(off)} = 4.2 \text{ V}$	$R_L = 3 \Omega$	$t_p = 20 \mu\text{s}$, dc $\leq 2\%$		7		μs

† Voltage and current values shown are nominal; exact values vary slightly with transistor parameters.

TYPICAL CHARACTERISTICS

TYPICAL DC CURRENT GAIN
VS
COLLECTOR CURRENT

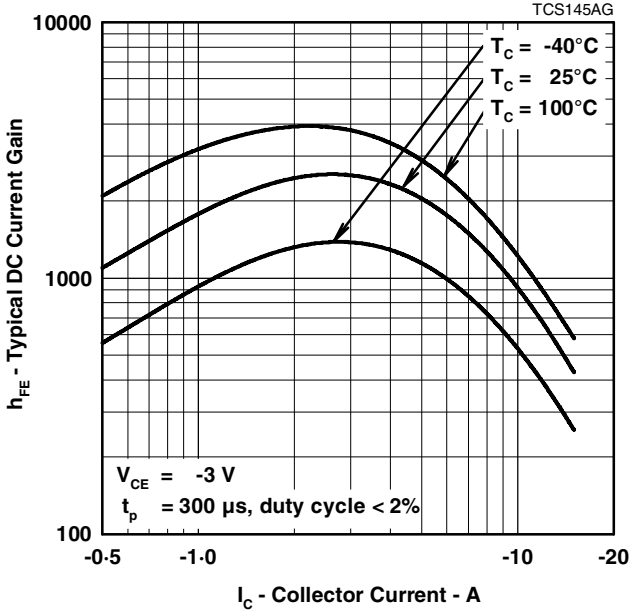


Figure 1.

COLLECTOR-EMITTER SATURATION VOLTAGE
VS
COLLECTOR CURRENT

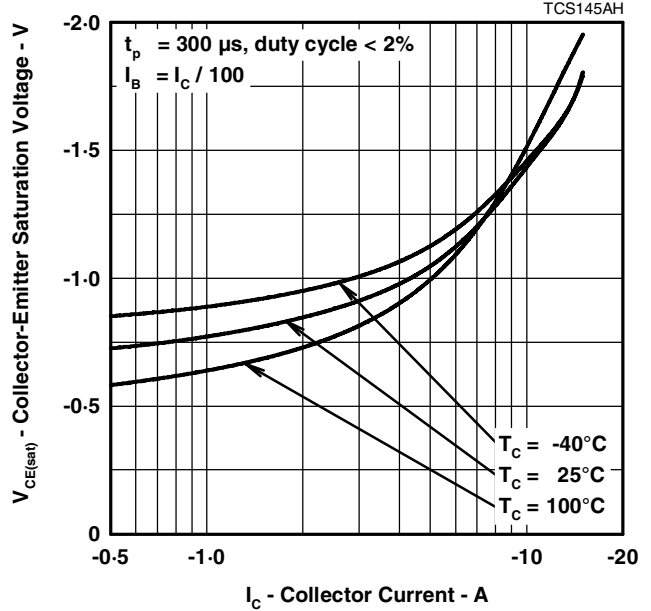


Figure 2.

BASE-EMITTER SATURATION VOLTAGE
VS
COLLECTOR CURRENT

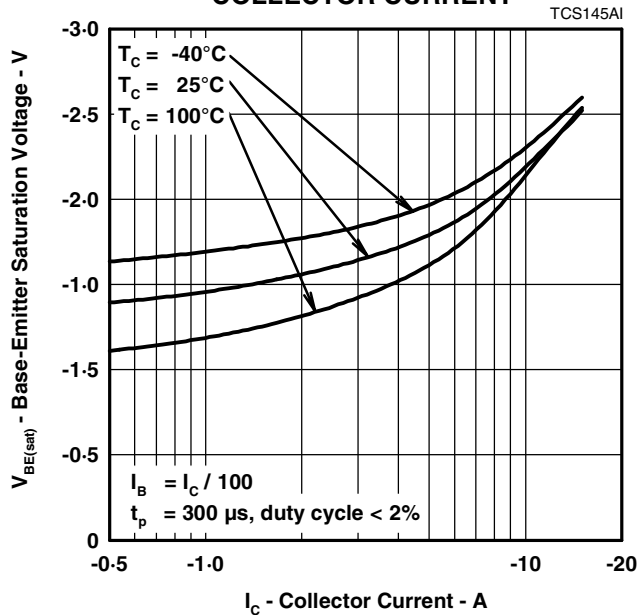


Figure 3.

PRODUCT INFORMATION

MAXIMUM SAFE OPERATING REGIONS

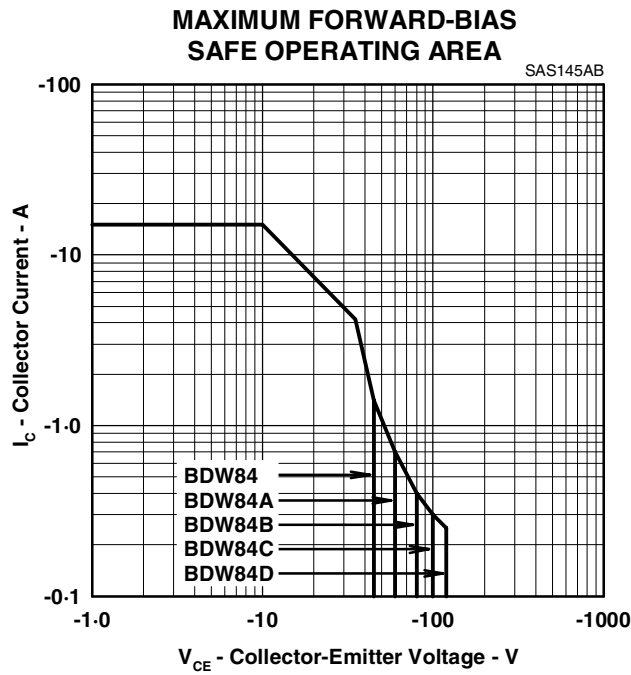


Figure 4.

THERMAL INFORMATION

**MAXIMUM POWER DISSIPATION
vs
CASE TEMPERATURE**

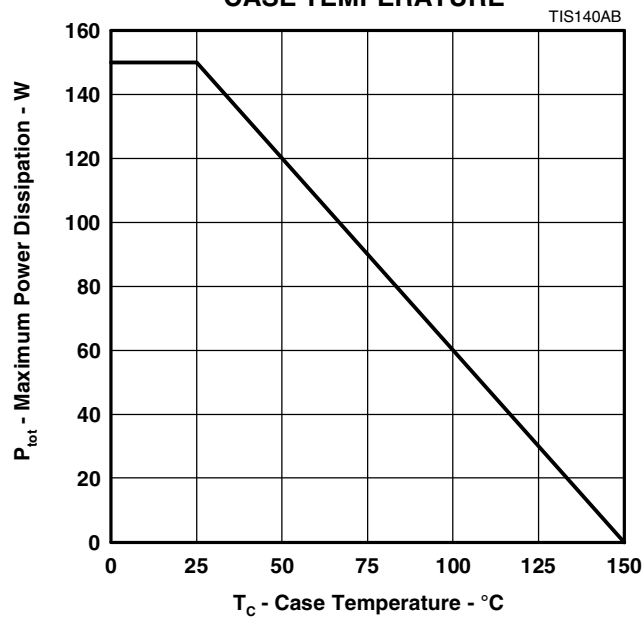


Figure 5.

PRODUCT INFORMATION